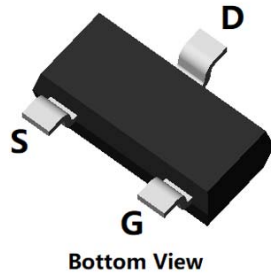
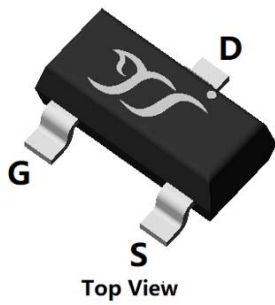
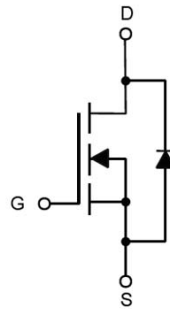


## N-Channel Enhancement Mode Field Effect Transistor



**SOT-23**



### Product Summary

- $V_{DS}$  20V
- $I_D$  3.0A
- $R_{DS(ON)}$ ( at  $V_{GS}=4.5V$ ) <50 mohm
- $R_{DS(ON)}$ ( at  $V_{GS}=2.5V$ ) <70 mohm

### General Description

- Trench Power LV MOSFET technology
- High Power and current handling capability
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

### Applications

- PWM application
- Load switch

### ■ Absolute Maximum Ratings ( $T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-source Voltage	$V_{DS}$	20	V
Gate-source Voltage	$V_{GS}$	$\pm 10$	V
Drain Current	$I_D$	$T_A=25^\circ C$ @ Steady State	3.0
		$T_A=70^\circ C$ @ Steady State	2.4
Pulsed Drain Current <sup>A</sup>	$I_{DM}$	14	A
Total Power Dissipation @ $T_A=25^\circ C$	$P_D$	0.7	W
Thermal Resistance Junction-to-Ambient @ Steady State <sup>B</sup>	$R_{\theta JA}$	178	$^\circ C/W$
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55~+150	$^\circ C$

### ■ Ordering Information (Example)

PREFERED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJL2302B	F2	2302B.	3000	30000	120000	7" reel

# YJL2302B

## ■ Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
<b>Static Parameter</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> =250μA	20			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V, T <sub>C</sub> =25°C			1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±10V, V <sub>DS</sub> =0V			±100	nA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> =250μA	0.55	0.78	1.1	V
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 4.5V, I <sub>D</sub> =3.0A		38.5	50	mΩ
		V <sub>GS</sub> = 2.5V, I <sub>D</sub> =2.0A		53.5	70	
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =3.0A, V <sub>GS</sub> =0V			1.2	V
Maximum Body-Diode Continuous Current	I <sub>S</sub>				3.0	A
<b>Dynamic Parameters</b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =10V, V <sub>GS</sub> =0V, f=1MHZ		220		pF
Output Capacitance	C <sub>oss</sub>			34		
Reverse Transfer Capacitance	C <sub>rss</sub>			26		
<b>Switching Parameters</b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>GS</sub> =4.5V, V <sub>DS</sub> =10V, I <sub>D</sub> =3.0A		3.61		nC
Gate Source Charge	Q <sub>gs</sub>			0.88		
Gate Drain Charge	Q <sub>gd</sub>			0.77		
Turn-on Delay Time	t <sub>D(on)</sub>	V <sub>GS</sub> =4.5V, V <sub>DD</sub> =10V, R <sub>L</sub> =1.5Ω, R <sub>GEN</sub> =3Ω		6.8		ns
Turn-on Rise Time	t <sub>r</sub>			57		
Turn-off Delay Time	t <sub>D(off)</sub>			14		
Turn-off Fall Time	t <sub>f</sub>			53		

A. Pulse Test: Pulse Width ≤ 300us, Duty cycle ≤ 2%.

B. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch.

## ■ Typical Performance Characteristics

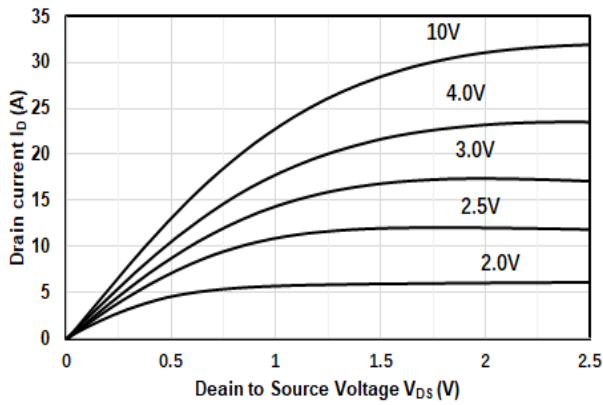


Figure1. Output Characteristics

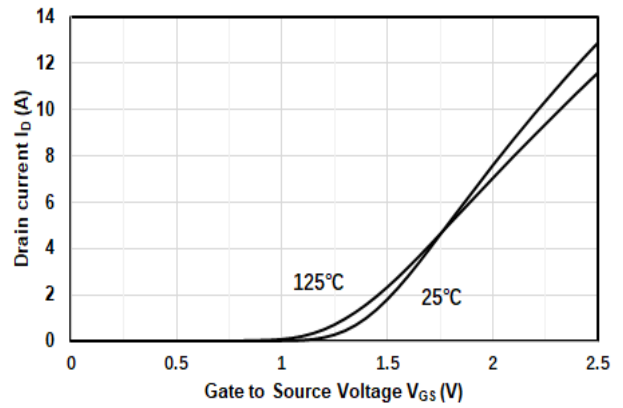


Figure2. Transfer Characteristics

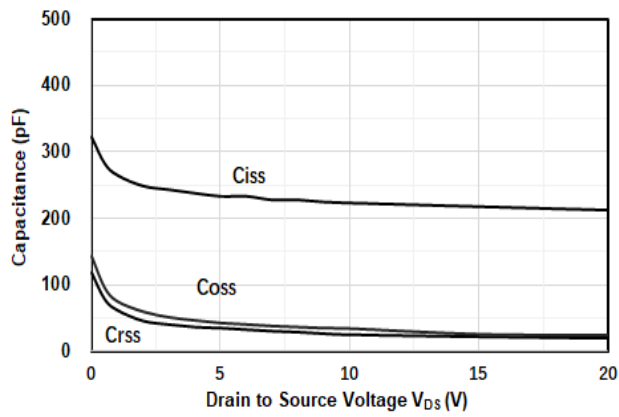


Figure3. Capacitance Characteristics

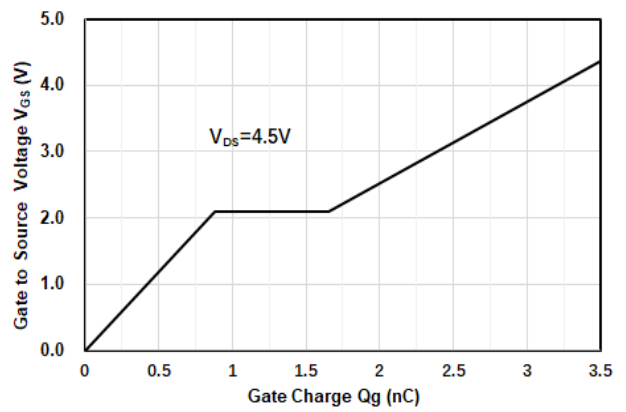


Figure4. Gate Charge

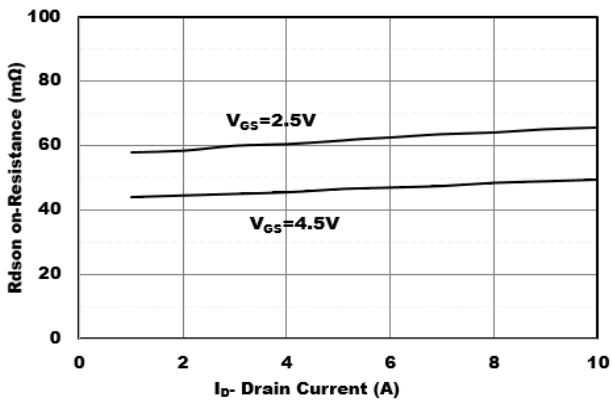


Figure5. Drain-Source on Resistance

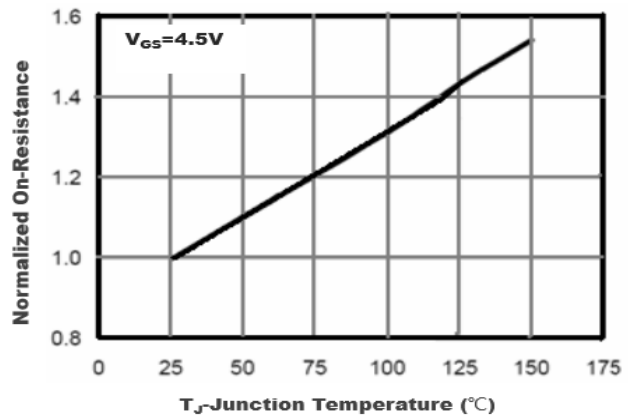


Figure6. Drain-Source on Resistance

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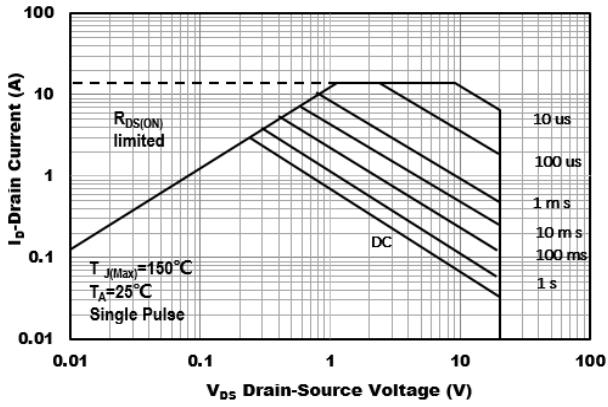


Figure 7. Safe Operation Area

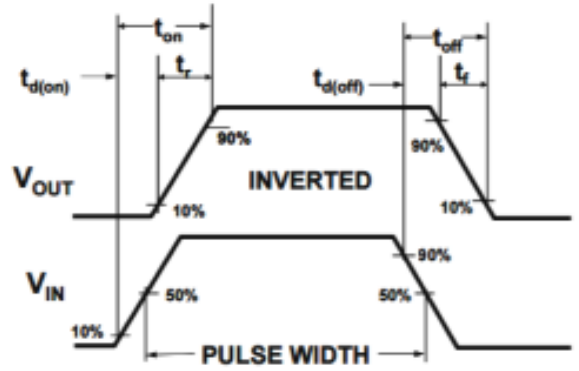


Figure 8. Switching wave

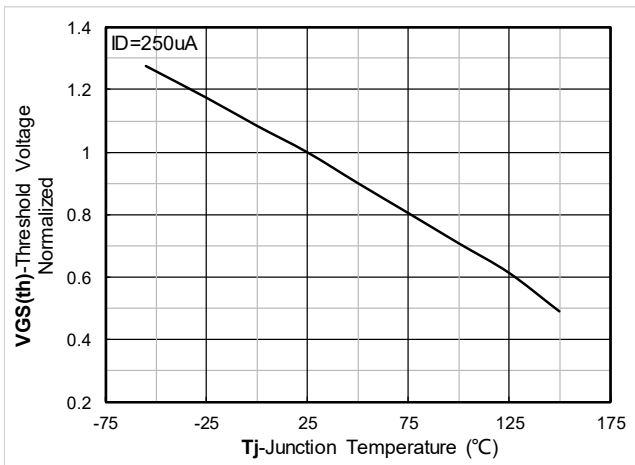


Figure 9. Normalized Threshold voltage

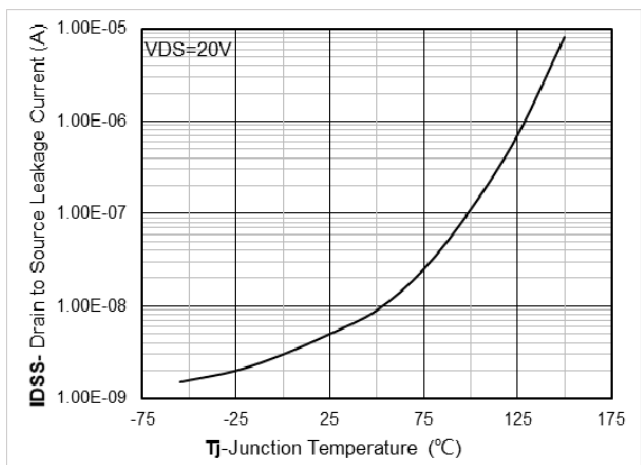
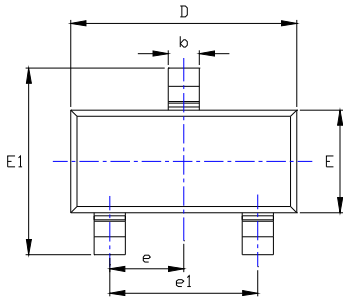


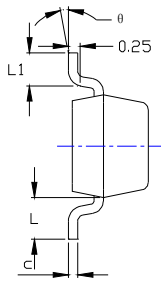
Figure 10. Drain to Source Leakage Current

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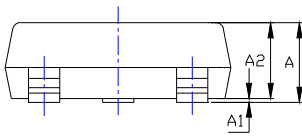
## ■SOT-23 Package information



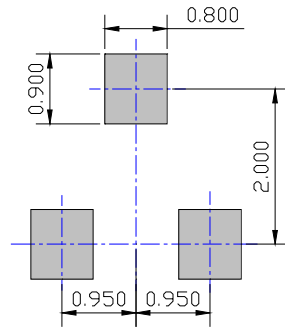
TOP VIEW



SIDE VIEW



SIDE VIEW



UNIT: mm

SUGGESTED SOLDER PAD LAYOUT

SYMBOL	DIMENSIONS			
	INCHES		Millimeter	
	MIN.	MAX.	MIN.	MAX.
A	0.035	0.045	0.900	1.150
A1	0.000	0.004	0.000	0.100
A2	0.035	0.041	0.900	1.050
b	0.012	0.020	0.300	0.500
c	0.004	0.008	0.100	0.200
D	0.110	0.118	2.800	3.000
E	0.047	0.055	1.200	1.400
E1	0.089	0.100	2.250	2.550
e	0.037TYP		0.950TYP	
e1	0.071	0.079	1.800	2.000
L	0.022REF		0.550REF	
L1	0.012	0.200	0.300	0.500
$\theta$	0°	8°	0°	8°

**NOTE:**

1.PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.

2.TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.

3.THE PAD LAYOUT IS FOR REFERENCE PURPOSES ONLY.

# YJL2302B

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